

BTA16-800CW

双向可控硅
TRIAC

版本号
201603-A

产品概述 GENERAL DESCRIPTION

BTA16-800CW 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

BTA16-800CW Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	≤ 35	mA

产品特性

- dv/dt高
- 通态压降低
- Rohs环保产品

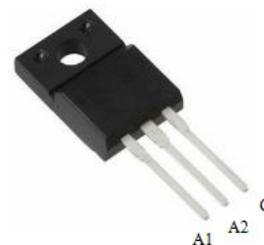
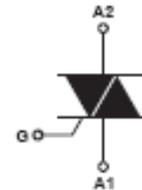
FEATURES

- Highly dv/dt
- Low on-state voltage
- Rohs Products

应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.



TO-220F

极限值(除非另有规定, T_j=25℃) ABSOLUTE RATINGS

(T_j=25℃, unless otherwise specified)

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
I _{T(RMS)}	RMS 通态电流 RMS on-state current (full sine wave)	T _C =86℃ 16	A
I _{TSM}	通态峰值浪涌电流 Non repetitive surge peak on-state current	F=50Hz, t=20ms 160	A
I ² t	I ² t 耗散值 I ² t value for fusing	T _p =10ms 144	A ² s
di/dt	通态电流上升值 Critical rate of rise of on-state current	F=120Hz, T _j =125℃ 50	A/μs
I _{GM}	门极峰值电流 Peak gate current	TP=20μs, T _j =125℃ 4	A
P _{G(AV)}	平均门极耗散功率 Average gate power dissipation	T _j =125℃ 1	W
T _{stg}	贮存结温范围 Storage junction temperature range	-40~+150	℃
T _j	工作结温范围 Operating junction temperature range	-40~+150	℃

电参数(除非另有规定, T_j=25℃) ELECTRICAL CHARACTERISTICS

(T_j=25℃, unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value	单位 Unit	测试条件 Test Conditions
触发电流 Gate trigger current	I _{GT} I ~ III	≤35	mA	V _D =12V, I _T =0.1A
触发电压 Gate trigger voltage	V _{GT} I ~ III	≤1.5	V	V _D =12V, I _T =0.1A
维持电流 Holding current	I _H	≤45	mA	V _D =12V, I _T =0.1A
擎住电流 Latching current	I _L	≤60	mA	V _D =12V, I _T =0.1A
电压上升率 Rise of off- state voltage	dv/dt	≥500	V/μS	V _D =67% V _{DRM}
通态压降 Peak on-state voltage	V _{TM}	≤1.65	V	I _T =22A
断态漏电流 Peak repetitive forward blocking current	I _{DRM}	≤5	μA	V _{RRM} =V _{DRM} , T _j = 25℃
	I _{RRM}	≤2	mA	V _{RRM} =V _{DRM} , T _j = 150℃

热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
R _{th(j-c)}	Junction to case(AC)	3.3	℃/W
R _{th(j-a)}	Junction to ambient	60	℃/W

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系
Fig.1.Maximum Power Dissipation Versus on-state current

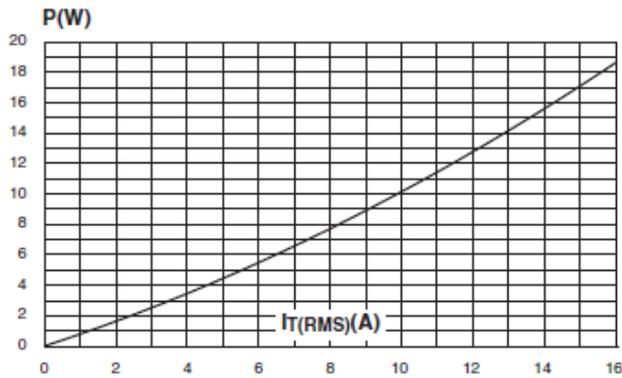


图2 RMS通态电流与Tc温度关系
Fig.2. RMS On-state Current Versus TL

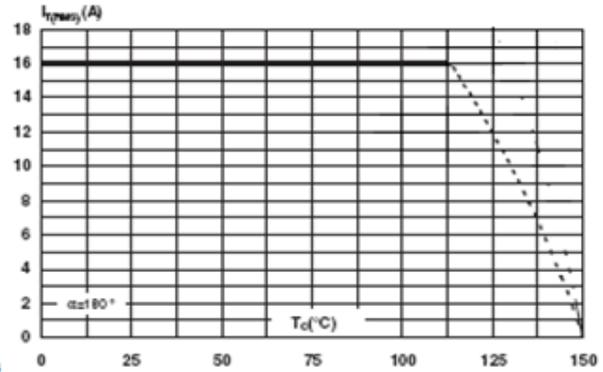


图3 通态特性
Fig.3.On-State Characteristics

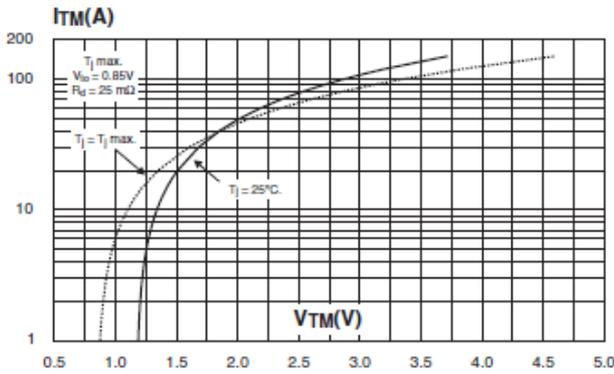


图4 通态浪涌峰值电流与周期数关系
Fig.4.Surge Peak On-state Current Versus Number Cycles

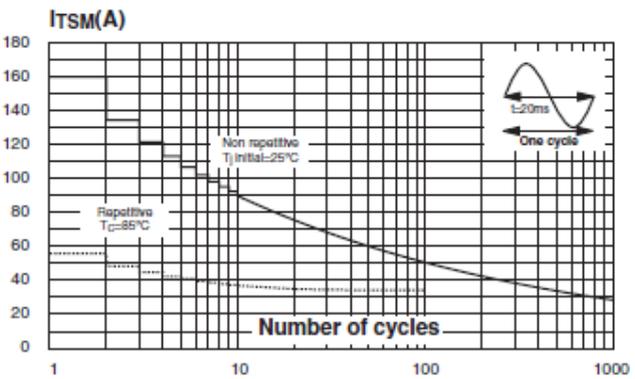
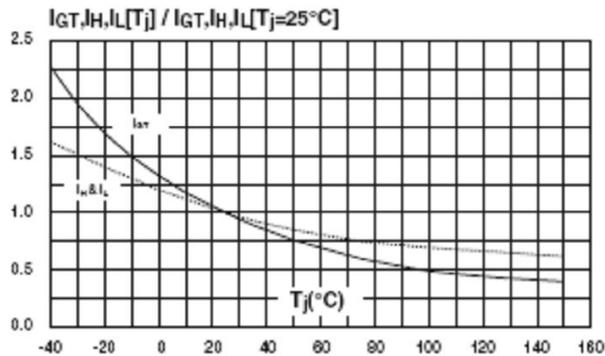
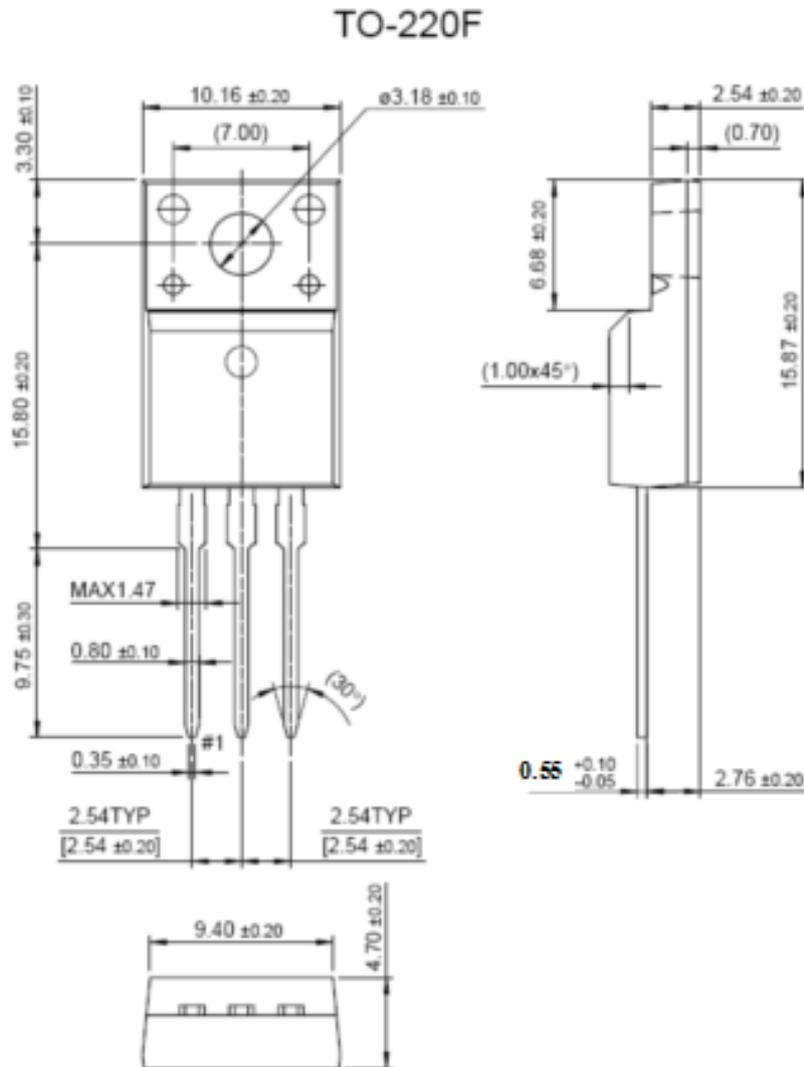


图5 IGT、IH、IL相对值（相对于25°C）与结温关系
Fig.5.Relative Variation Of Gate Trigger Current , Holding Current And Latching Current Versus Junction Temperature (Typical Value)



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